PCN Number: 2		20160	20160331001 <mark>A</mark>			PCN Date: 4/18/2016											
Title: Qualification of 0 process technology			CFAB as an additional wafer fab site option for				or select devices in LBC5										
Customer Contact:		<u>PC</u>	<u>N Manager</u>		Dept	:	Qu	ality Serv	ices								
Proposed 1 st Ship Date:		: 7/8	/2016	Estimated Availabilit				oate provi ample ree									
Ch	ange Ty	/pe:															
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	Test S	ite		Packing/Sh	ipping/Labeli	ng	Te	Test Process									
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ina	dverte	ntly listed in	page 2	<mark>, but not in th</mark>	e Product A	ffected So	ectio	<mark>n in pa</mark>	ige 3.								
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							_				Please refer to the Product Affected Section on the following:						
	Group 1: Devices that may appear in notification letter, page 2. These are not affected by																
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New			
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
CFAB	CU3	CHN	Chengdu

Sample product shipping label (not actual product label)



Product Affected:

TAS5721DCA	TAS5731MPHP	TAS5731PHP	
TAS5721DCAR	TAS5731MPHPR	TAS5731PHPR	
Group 2: This is correct	. Original devices listed in	Product Affected Sectio	n, 4/8/16 notification. These
are still affected by this	change.		
CXD9981TNDDV	TAS5342LAADDVR	TAS5614ADKD	TAS5708PHPR
CXD9981TNDDVR	TAS5352ADDV	TAS5614ADKDR	TAS5710PHP
CXD9981UTNDDV	TAS5352ADDVR	TAS5614APHD	TAS5710PHPR
CXD9981UTNDDVR	TAS5613ADKD	TAS5614APHDR	TPA3251D2DDV
TAS5342ADDV	TAS5613ADKDR	TAS5708LPHP	TPA3251D2DDVR
TAS5342ADDVR	TAS5613APHD	TAS5708LPHPR	TPS65149RSHR
TAS5342LAADDV	TAS5613APHDR	TAS5708PHP	TPS65155RKPR

Qualification Report

Qualification of LBC5 Process Technology at CFAB Approved 03/02/2012

Die Attributes

Attributes	Process QBS : TAS5613APHD Approved: 3/2/2012	Process QBS: DRV8813A0PWP Approved: 3/2/2012	Process QBS: SN8C0183PWP Approved: 3/2/2012
Wafer Fab Site	CFAB	CFAB	CFAB
Wafer Fab Process	LBC5	LBC5	LBC5
Wafer Diameter	200mm	200mm	200mm

- QBS: Qual By Similarity

- Qual Device TAS5613APHD and SN8C0183PWP are qualified at LEVEL3-260C

- Qual Device DRV8813A0PWP is qualified at LEVEL1-260C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: TAS5613APHD	Qual Device: DRV8813A0PWP	Qual Device: SN8C0183PWP
AC	Autoclave 121C	96 Hours	3/77/0	3/77/0	-
ED	Electrical Characterization	Per Datasheet Parameters	3/Pass	3/Pass	3/3/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/77/0	-	-
HBM	ESD - HBM	1500 V	3/21/0	1/3/0	-
CDM	ESD - CDM	250 V	3/15/0	1/3/0	-
HTOL	Life Test, 155C	240 Hours	3/77/0		3/77/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/77/0	-	_
LU	Latch-up	(per JESD78)	3/6/0	1/6/0	-
тс	Temperature Cycle, -65/150C	500 Cycles	3/77/0	3/77/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

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